

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Amended) A circuit device manufacturing method comprising:
 - forming conductive films that are laminated in multiple layers with interlayer insulating layers interposed in between;
 - forming a first conductive wiring layer by selective removal of the conductive film at a top surface;
 - forming through holes in the interlayer insulating layers and forming connection means in the through holes to electrically connect the first conductive wiring layer with the conductive film at a rear surface;
 - affixing a circuit element to the first conductive wiring layer and electrically connecting the circuit element to the first conductive wiring layer via conductive wires;
 - irradiating plasma onto the first conductive wiring layer, including the circuit element and the conductive wires; and
 - forming a resin layer so as to cover the circuit element; and
forming a second conductive wiring layer by selective removal of the conductive film at the rear surface after the irradiation.
2. (Currently amended) The method of Claim 1, wherein the conductive wiring layer is covered with resin while exposing locations that are to become pads.
3. (Original) The method of Claim 2, wherein in the step of irradiating plasma, the plasma is irradiated onto a top surface of the resin as well to roughen the top surface of the resin

while a voltage, which is charged up in the resin, is released from the conductive wiring layer and via the conductive films.

4. (Original) The method of Claim 1, wherein connection means, comprising a plating film, are formed in the through holes to electrically connect the conductive wiring layer and the conductive film.

5. (Original) The method of Claim 1, wherein the plasma irradiation is carried out using oxygen gas or ozone.

6. (Original) The method of Claim 1, wherein the plasma irradiation is carried out using an inert gas, such as argon, neon, or helium.

7. (Original) The method of Claim 6, wherein in the process of irradiating the plasma using argon, ion energy of argon is in a range of 40eV to 100eV.

8. (Currently amended) The method of Claim 1, wherein the plasma irradiation includes using an oxygen gas and wherein, after performing the plasma irradiation using oxygen gas, plasma irradiation using an inert gas, such as argon, neon, or helium, is carried out.

9. (Original) The method of Claim 1, wherein the conductive film is formed of a metal having copper as a principal material.

10. (Original) The method of Claim 1, wherein the circuit element is semiconductor element that is electrically connected via metal wires to the conductive wiring layer.

11. (Original) The method of Claim 1, wherein the circuit element is semiconductor element that is mounted in a face-down manner.

12. (Original) The method of Claim 11, wherein the circuit element is electrically connected to the conductive wiring layer via soft solder or other solder material.

13. (Original) The method of Claim 1, wherein after the plasma irradiation, the conductive film at the rear surface is removed selectively to form a conductive wiring layer.

14. (New) The method of Claim 1 wherein the first conductive wiring layer is covered by overcoat resin.